

BSS139Z

0.2A, 50V N-CHANNEL **POWER MOSFET**

DESCRIPTION

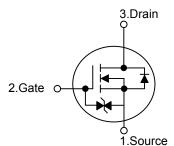
The UTC BSS139Z is an N-Channel power MOSFET, it uses UTC's advanced technology to provide customers with high switching speed and low threshold voltage.

The UTC BSS139Z is suitable for battery-powered products, power management in portable and DC to DC converters, etc.

FEATURES

- * $R_{DS(ON)}$ < 5.6 Ω @ V_{GS} =5V, I_D =200mA
- * High switching speed
- * Low threshold voltage (Min.=0.5V, Max.=1.5V)

SYMBOL



ORDERING	INFORMATION					
Ordering Number		Dookogo	Pin	Assignm	Decking	
BSS139ZG- <u>AE2</u> -R		Package	1	2	3	Packing
E	SOT-23-3	S	G	D	Tape Reel	
Note: Pin Assignr	ment: G: Gate D: Drain S: Source					
BSS139ZG- <u>AE</u> T	Ξ2-R					
(1)Packing Type		(1) R: Tape Re	eel			

(2) AE2: SOT-23-3

(3) G: Halogen Free and Lead Free

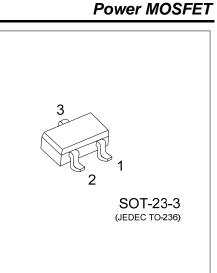
(2)Package Type

- (3)Green Package

MARKING

Ν





■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER			SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	50	V		
Gate-Source Voltage		V _{GSS}	±20	V		
Drain Current	Continuous I _D		I _D	200	mA	
	Pulsed	t _p ≤10µs	I _{DM}	800	mA	
Power Dissipation		PD	225	mW		
Junction Temperature		TJ	-55~+150	°C		
Storage Temperature Range		T _{STG}	-55~+150	°C		

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	556	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μΑ, V _{GS} =0V	50			V	
Drain Source Lookage Current			V _{DS} =25V, V _{GS} =0V			0.1	μA
Drain-Source Leakage Current		IDSS	V _{DS} =50V, V _{GS} =0V			0.5	μA
	Forward	- I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+10	μA
Gate-Source Leakage Current	Reverse		V _{GS} =-20V, V _{DS} =0V			-10	μA
ON CHARACTERISTICS (Note 1)							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =1.0mA	0.5		1.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =2.75V, I _D =200mA		5.6	10	Ω
			V _{GS} =5.0V, I _D =200mA			3.5	Ω
DYNAMIC PARAMETERS							
Input Capacitance		CISS			40	50	pF
Output Capacitance		C _{OSS}	−V _{GS} =0V, V _{DS} =25V, −f=1.0MHz		12	25	pF
Reverse Transfer Capacitance		C _{RSS}			3.5	5.0	рF
SWITCHING PARAMETERS (Not	e 2)						
Turn-ON Delay Time		t _{D(ON)}				20	ns
Turn-OFF Delay Time		t _{D(OFF)}	$-V_{DD}=30V, I_{D}=0.2A$			20	ns
Notoo: 1. Duloo Toot: Duloo width c	2000 Dut		-		•	•	

Notes: 1. Pulse Test: Pulse width \leq 300µs, Duty cycle \leq 2%.

2. Switching characteristics are independent of operating junction temperature.



0.3

0.6

0.9

0.6

0.8

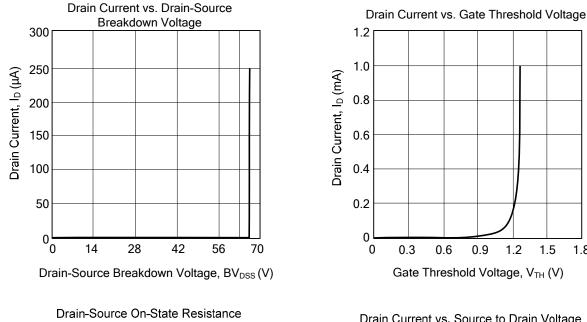
1.0

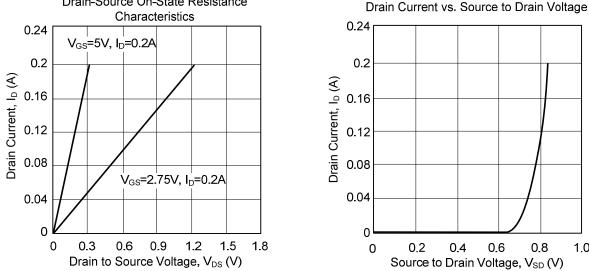
1.2

1.5

1.8

TYPICAL CHARACTERISTICS





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